

b. Amendments to the Specification

Please rewrite the paragraph between page 16, line 30, and page 17, line 2, as follows:

[.] The MOMB growth is stopped when n-type InP collector layer 98' has a thickness of 1,500 Å - 2,500 Å. After the MOMB growth, a wash with the same aqueous HF solution removes the SiO₂ mask thereby producing structure 74' of Figure 10. The resulting collector layer 98' has a limited lateral extent, which produces a nontrivial cross-sectional profile.